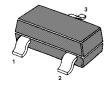
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

For low current rectification

Features

- High reliability
- Low reverse current





Marking Code: "ZE" SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

| Parameter | Symbol | Value | Unit |
|---|------------------|---------------|------|
| Repetitive Peak Reverse Voltage | V_{RM} | 45 | V |
| Reverse Voltage | V _R | 40 | V |
| Average Rectified Forward Current | Io | 30 | mA |
| Peak Forward Surge Current (t = 8.3 ms) | I _{FSM} | 200 | mA |
| Junction Temperature | T _j | 125 | °C |
| Storage Temperature Range | T _{stg} | - 55 to + 125 | °C |

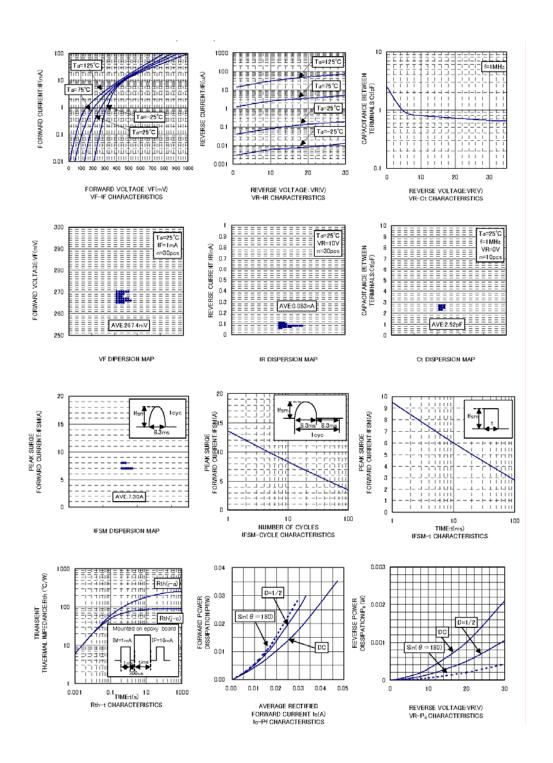
Characteristics at T_a = 25 °C

| Parameter | Symbol | Min. | Тур. | Max. | Unit |
|--|--------------------|------|------|------|------|
| Forward Voltage at I _F = 1 mA | V _F | ı | - | 0.37 | V |
| Reverse Current at V _R = 10 V | I _R | - | - | 1 | μΑ |
| Reverse Breakdown Voltage at I _R = 10 μA | V _{(BR)R} | 45 | - | - | V |
| Capacitance between Terminals at $V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$ | Ст | - | 2 | - | pF |











SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







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